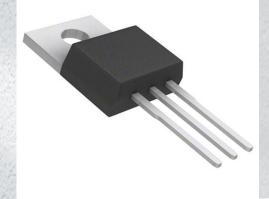


# **PSMN8R5-100PSQ Datasheet**

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DiGi Electronics Part Number Manufacturer

Manufacturer Product Number

Description

**Detailed Description** 

PSMN8R5-100PSQ-DG Nexperia USA Inc. PSMN8R5-100PSQ MOSFET N-CH 100V 100A TO220AB

N-Channel 100 V 100A (Tj) 263W (Tc) Through Hole TO-220AB

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# Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
PSMN8R5-100PSQ	Nexperia USA Inc.
Series:	Product Status:
	Obsolete
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
100 V	100A (Tj)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ ld, Vgs:
10V	8.5mOhm @ 25A, 10V
Vgs(th) (Max) @ ld:	Gate Charge (Qg) (Max) @ Vgs:
4V @ 1mA	111 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±20V	5512 pF @ 50 V
FET Feature:	Power Dissipation (Max):
-	263W (Tc)
Operating Temperature:	Mounting Type:
-55°C ~ 175°C (TJ)	Through Hole
Supplier Device Package:	Package / Case:
ТО-220АВ	TO-220-3
Base Product Number:	
PSMN8R5	

# **Environmental & Export classification**

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.29.0095	



# **PSMN8R5-100PS**

N-channel 100 V 8.5 mΩ standard level MOSFET in TO22017 October 2013Product data sheet

## 1. General description

Standard level N-channel MOSFET in a TO220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

## 2. Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

## 3. Applications

- AC-to-DC power supply equipment
- Motor control
- Server power supplies
- Synchronous rectification

## 4. Quick reference data

Table 1. Qu	iick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	100	V
I <sub>D</sub>	drain current	T <sub>j</sub> = 25 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u>	[1]	-	-	100	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	-	263	W
Static charac	teristics	·	1			- 1	
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 13; Fig. 12		4.5	6.4	8.5	mΩ
Dynamic cha	racteristics	·	1				
Q <sub>GD</sub>	gate-drain charge	$V_{GS}$ = 10 V; I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V;		-	33	-	nC
Q <sub>G(tot)</sub>	total gate charge	<u>Fig. 14; Fig. 15</u>		-	111	-	nC
Avalanche R	uggedness		1				
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$\label{eq:VGS} \begin{split} V_{GS} &= 10 \text{ V};  \text{T}_{j(\text{init})} = 25 ^{\circ}\text{C};  \text{I}_{\text{D}} = 100 \text{ A}; \\ V_{sup} &\leq 100 \text{ V};  \text{R}_{\text{GS}} = 50  \Omega; \text{ unclamped}; \\ \hline \text{Fig. 3} \end{split}$		-	-	219	mJ

[1] Continious current limited by package.

# nexperia

# PSMN8R5-100PS

#### N-channel 100 V 8.5 m $\Omega$ standard level MOSFET in TO220

## 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain		
3	S	source		G-UF44
mb	D	mounting base; connected to drain		mbb076 S
			TO-220AB (SOT78)	

# 6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
PSMN8R5-100PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78			

## 7. Marking

Table 4. Marking codes	
Type number	Marking code
PSMN8R5-100PS	PSMN8R5-100PS

# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	100	V
V <sub>DGR</sub>	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		-	100	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>j</sub> = 25 °C; <u>Fig. 1</u>	[1]	-	100	А
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 1</u>		-	75	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$ ; Fig. 4		-	429	А

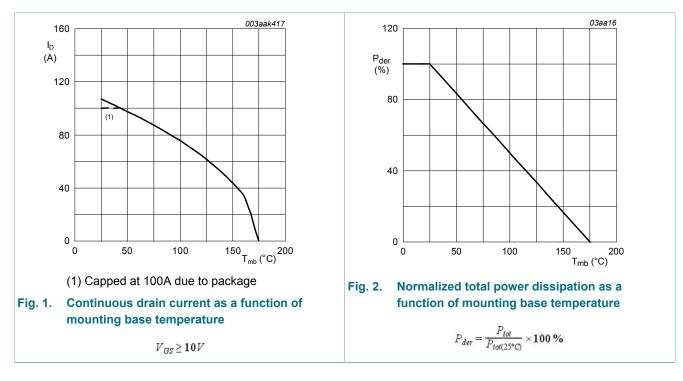
PSMN8R5-100PS

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# PSMN8R5-100PS

#### N-channel 100 V 8.5 m $\Omega$ standard level MOSFET in TO220

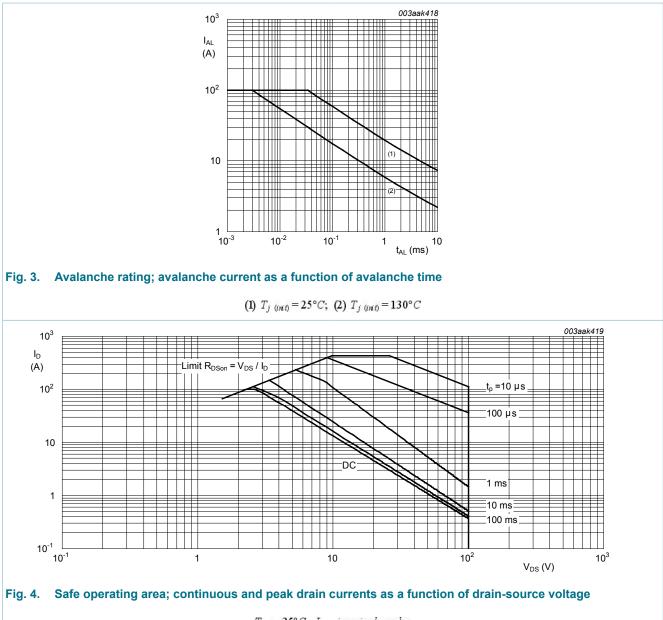
Symbol	Parameter	Conditions		Min	Мах	Unit
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	263	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
Source-dra	in diode		-			
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	100	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^\circ C$		-	429	А
Avalanche	Ruggedness		_			
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \; V; \; T_{j(init)} = 25 \; ^\circC; \; I_D = 100 \; A; \\ V_{sup} \leq 100 \; V; \; R_{GS} = 50 \; \Omega; \; unclamped; \\ \hline Fig. 3 \end{array}$		-	219	mJ



[1] Continious current limited by package.

# PSMN8R5-100PS

#### N-channel 100 V 8.5 m $\Omega$ standard level MOSFET in TO220



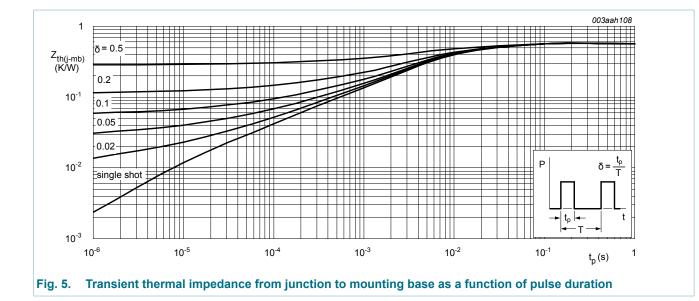
 $T_{mb} = 25^{\circ}C; \ I_{DM}$  is a single pulse

## 9. Thermal characteristics

Table 6. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	0.49	0.57	K/W

# PSMN8R5-100PS

#### N-channel 100 V 8.5 m $\Omega$ standard level MOSFET in TO220



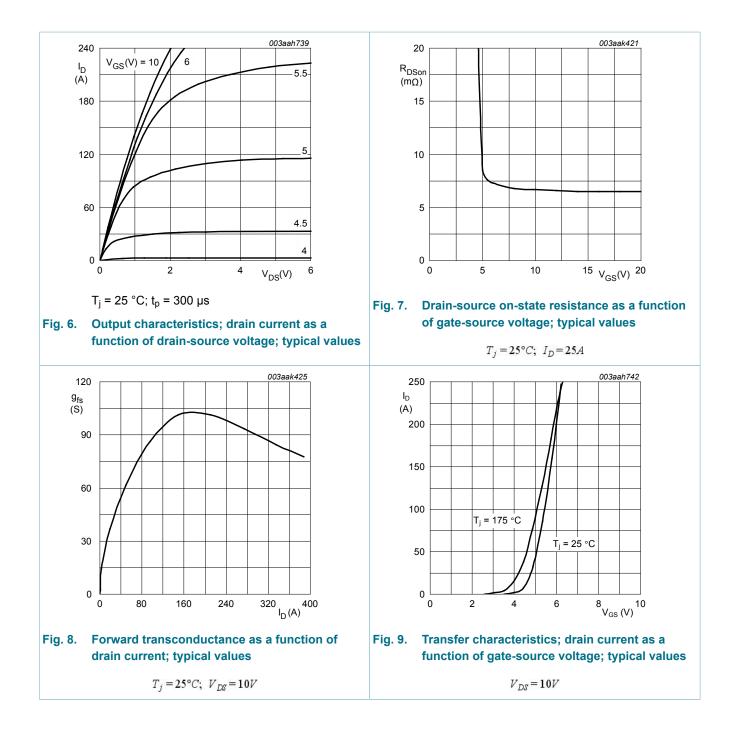
## **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	100	-	-	V
breakdown voltage	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = -55 °C	90	-	-	V	
V <sub>GS(th)</sub>	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C; Fig. 10; Fig. 11	2.4	3	4	V
V <sub>GSth</sub> gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; Fig. 10	1	-	-	V	
	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10	-	-	4.5	V	
I <sub>DSS</sub> drain leakage current	$V_{DS}$ = 100 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	0.02	1	μA	
	V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 100 °C	-	-	20	μA	
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
		$V_{GS}$ = 20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; Fig. 12	-	16.95	22.6	mΩ
	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 100 °C; Fig. 12	-	11.18	14.9	mΩ	
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 13; Fig. 12	4.5	6.4	8.5	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz	0.36	0.71	1.42	Ω

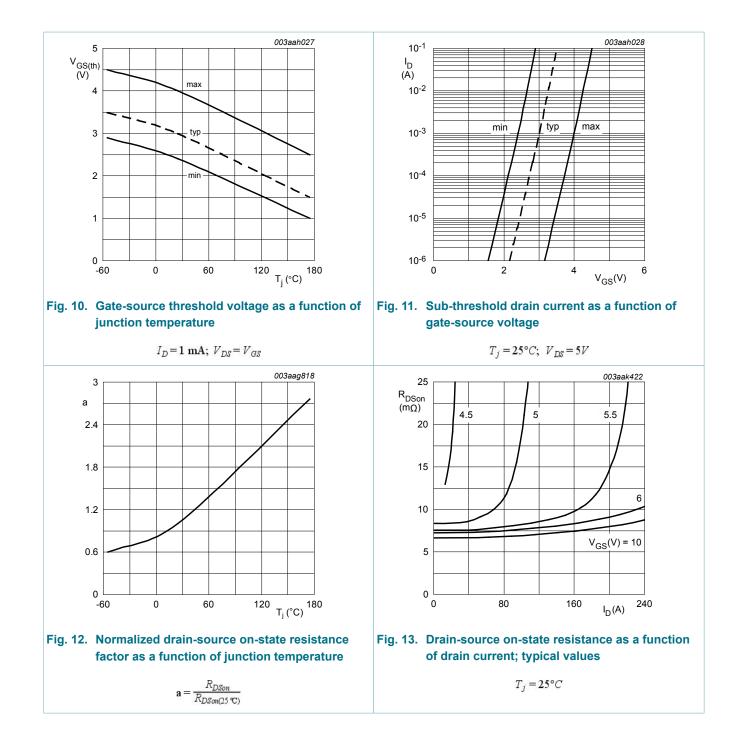
# PSMN8R5-100PS

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic ch	aracteristics	· · · · · ·				
Q <sub>G(tot)</sub>	total gate charge	$I_D$ = 25 A; $V_{DS}$ = 50 V; $V_{GS}$ = 10 V;	-	111	-	nC
Q <sub>GS</sub>	gate-source charge	<u>Fig. 14; Fig. 15</u>	-	24	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate- source charge	-	-	16	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate- source charge		-	8	-	nC
Q <sub>GD</sub>	gate-drain charge		-	33	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	I <sub>D</sub> = 15 A; V <sub>DS</sub> = 50 V; <u>Fig. 14; Fig. 15</u>	-	4.4	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 0 V; f = 1 MHz; T <sub>j</sub> = 25 °C; <u>Fig. 16</u> ; <u>Fig. 17</u>	-	5512	-	pF
C <sub>oss</sub>	output capacitance	V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 0 V; f = 1 MHz; T <sub>j</sub> = 25 °C; <u>Fig. 17</u>	-	380	-	pF
C <sub>rss</sub>	reverse transfer capacitance	V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 0 V; f = 1 MHz; T <sub>j</sub> = 25 °C; <u>Fig. 16</u> ; <u>Fig. 17</u>	-	256	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 50 V; R <sub>L</sub> = 2 Ω; V <sub>GS</sub> = 10 V;	-	20	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega$	-	35	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	87	-	ns
t <sub>f</sub>	fall time		-	43	-	ns
Source-drai	in diode	· · · · · · · · · · · · · · · · · · ·				
V <sub>SD</sub>	source-drain voltage	$I_{S}$ = 25 A; $V_{GS}$ = 0 V; $T_{j}$ = 25 °C; <u>Fig. 18</u>	-	0.82	1.2	V
t <sub>rr</sub>	reverse recovery time	I <sub>S</sub> = 25 A; dI <sub>S</sub> /dt = -100 A/µs; V <sub>GS</sub> = 0 V;	-	53	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 50 V	-	124	-	nC

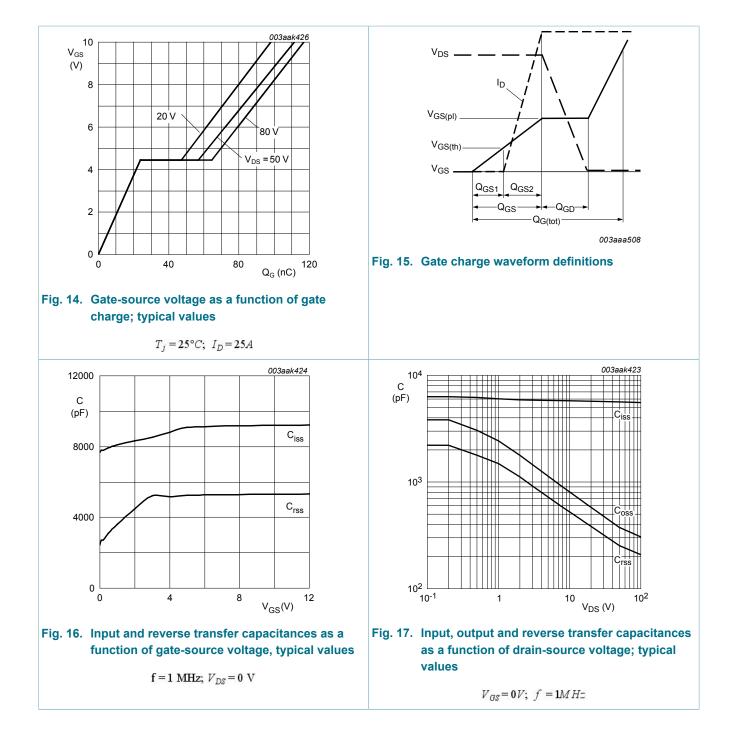
# PSMN8R5-100PS



# PSMN8R5-100PS

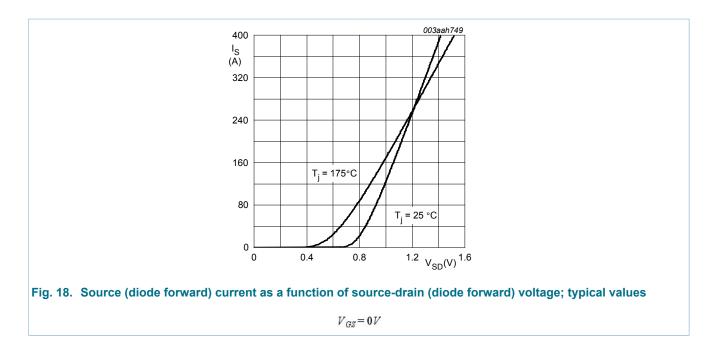


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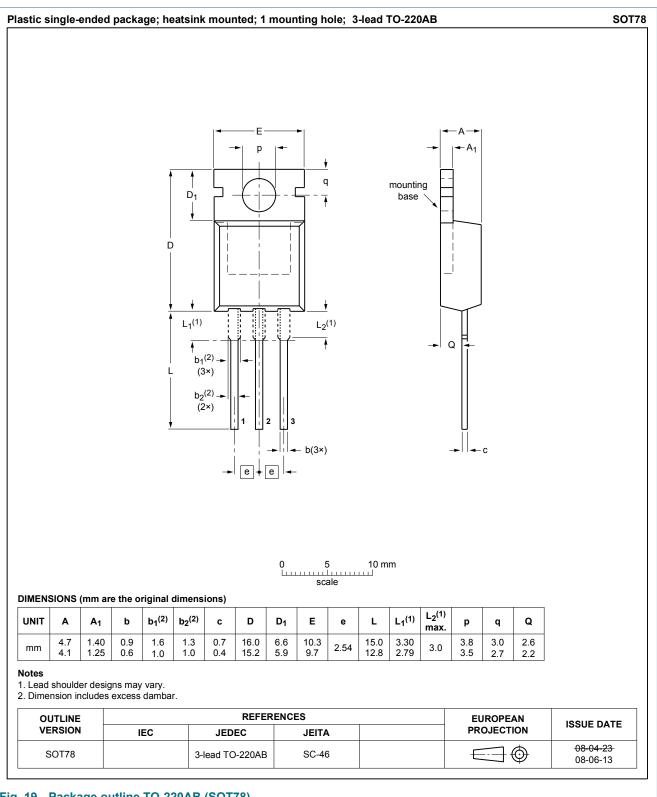
#### N-channel 100 V 8.5 m $\Omega$ standard level MOSFET in TO220



# PSMN8R5-100PS

N-channel 100 V 8.5 m $\Omega$  standard level MOSFET in TO220

## 11. Package outline



#### Fig. 19. Package outline TO-220AB (SOT78)

PSMN8R5-100PS

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#### N-channel 100 V 8.5 m $\Omega$ standard level MOSFET in TO220

### 12. Legal information

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Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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[2] The term 'short data sheet' is explained in section "Definitions".

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# PSMN8R5-100PS

#### N-channel 100 V 8.5 m $\Omega$ standard level MOSFET in TO220

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#### N-channel 100 V 8.5 m $\Omega$ standard level MOSFET in TO220

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